YZPST-BT151 SCRs

●Main Feature (Tj=25℃)

Symbol	Value	Unit
$I_{T(AV)}$	7.5	A
V_{DRM} / V_{RRM}	⩾ 600	V
I_{GT}	1 to 20	mA

●Absolute ratings (Limiting Values)

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	12	A
$I_{T(AV)}$	AV on-state current (180° conduction angle)	7.5	A
I_{TSM}	Non repetitive surge peak on-state Current (tp=10ms)	100	A
I^2t	(tp=10ms)	50	A^2S
I_{GM}	Peak gate current(tp=20us)	2	A
P_{GM}	Peak gate power	5	W
$P_{G(AV)}$	Average gate power	0.5	W
Tstg Tj	Storage temperature Operating junction temperature	-40--+150 -40--+125	℃

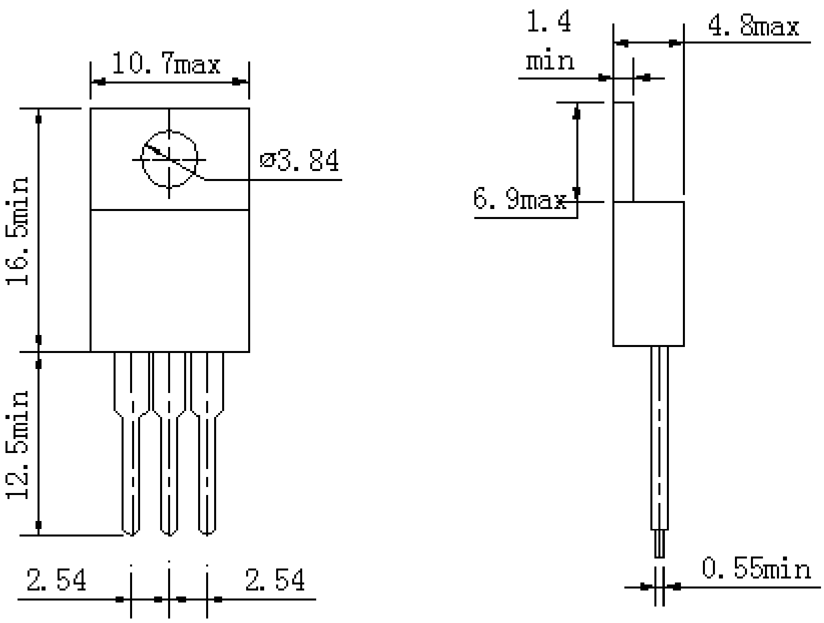
●Thermai Resistances

Symbol	Parameter	Value	Unit
Rth (j-c)	Junction to case	1.3	K/W
Rth (j-a)	Junction to ambient	60	K/W

●Electrical characteristics (Tj=25℃ unless otherwise stated)

Symbol	Test Conditions		Value			Unit
			Min	Type	Max	
I_{GT}	V_D=6V, R_L=100Ω		1	5	20	uA
V_{GT}	V_D=12V, R_L=100Ω		-----	0.7	0.8	V
V_{GD}	$V_D=V_{DRM}$, R_L=3.3KΩ Tj=110℃		0.2	-----	-----	V
I_H	I_T=100mA Gate Open		-----	9	20	mA
dV/dt	V_D=67%V_{DRM}, GateOpen, Tj=125℃		50	125	-----	v/μs
V_{TM}	I_T=16A,tp=380μs		-----	-----	1.7	V
I_{DRM} I_{RRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	T_j=25℃	-----	-----	20	uA
		T_j=110℃	-----	-----	300	uA

●Measure of package (TO-220E)



●Electrocircuit: